



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
-20V	110m Ω @ V _{GS} = -4.5V	SOT23	-2.6A
-20V	225mΩ @ V_{GS} = -2.5 V	30123	-2.0A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{\text{DS(ON)}}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

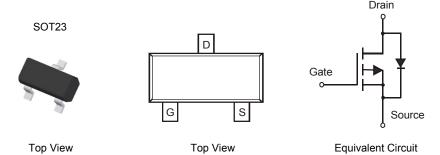
- General Purpose Interfacing Switch
- Power Management Functions

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Ordering Information(Note 4& 5)

Part Number	Qualification	Case	Packaging
DMP2225L-7	Standard	SOT-23	3000/Tape & Reel
DMP2225LQ-7	Automotive	SOT-23	3000/Tape & Reel

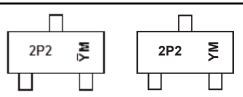
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Shanghai A/T Site

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Chengdu A/T Site

2P2 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

 $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteri	stic		Symbol	Value	Units
Drain-Source Voltage		$V_{ extsf{DSS}}$	-20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note 6) Stead $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	-2.6 -2	А
Pulsed Drain Current (Note 7)		I _{DM}	8	Α	

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P_{D}	1.08	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{0JA}	115	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

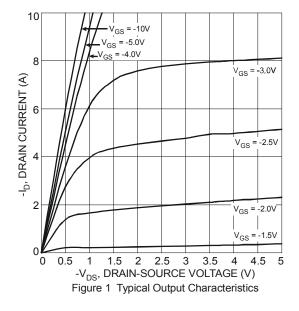
Electrical Characteristics (@T_A = ±25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)		•		•		
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-800	nA	$V_{DS} = -20V, V_{GS} = 0V$
On-State Drain Current		-6	_	_	Α	$V_{DS} \le -5V, V_{GS} = -4.5V$
On-State Drain Current	I _{D(ON)}	-3	_	_		$V_{DS} \le -5V, V_{GS} = -2.5V$
Gate-Source Leakage	I _{GSS}	_	_	±80	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-0.45	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance		_	80	110	mΩ	$V_{GS} = -4.5V$, $I_D = -2.6A$
Static Dialii-Source Off-Resistance	R _{DS} (ON)		165	225		$V_{GS} = -2.5V$, $I_D = -2.0A$
Forward Transfer Admittance	Y _{fs}	_	4	_	S	$V_{DS} = -5V, I_{D} = -2.6A$
Diode Forward Voltage (Note 7)	V_{SD}	_	_	-1.26	V	$V_{GS} = 0V, I_{S} = -2.6A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	250	_	pF	10)/ 1/
Output Capacitance	Coss	_	88	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	58	_	pF	1 - 1.000112
Gate Resistance	Rg	_	12	16	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	4.3	5.3		V - 45V V - 40V
Gate-Source Charge	Q _{gs}		0.9	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -2.7A$
Gate-Drain Charge	Q_{gd}	_	2.1	_		ID2.1A

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





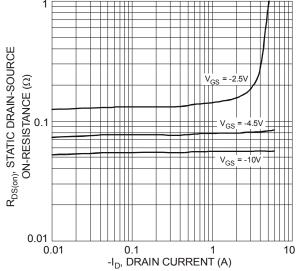


Figure 3 On-Resistance vs. Drain Current and Gate Voltage

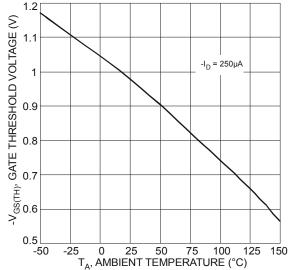
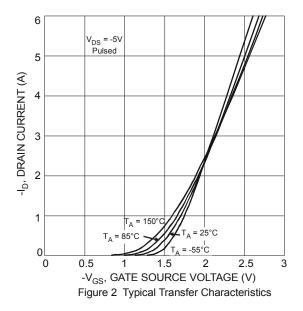
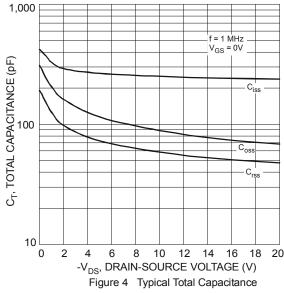


Figure 5 Gate Threshold Voltage vs. Ambient Temperature





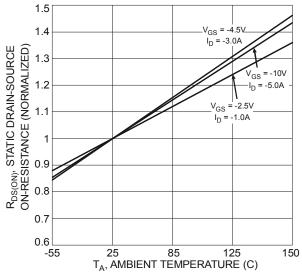


Figure 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



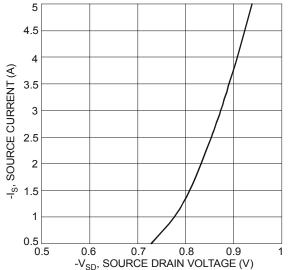
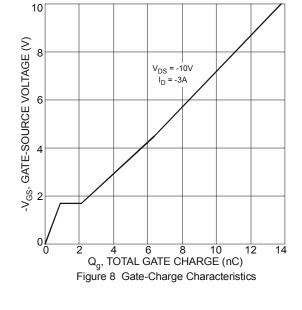
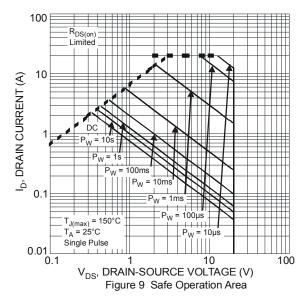
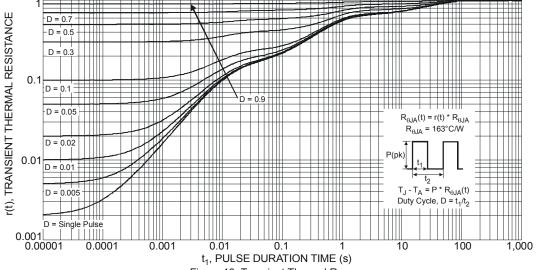


Figure 7 Reverse Drain Current vs. Source-Drain Voltage



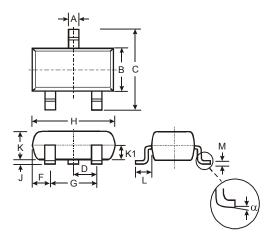






Package Outline Dimensions

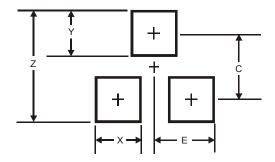
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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